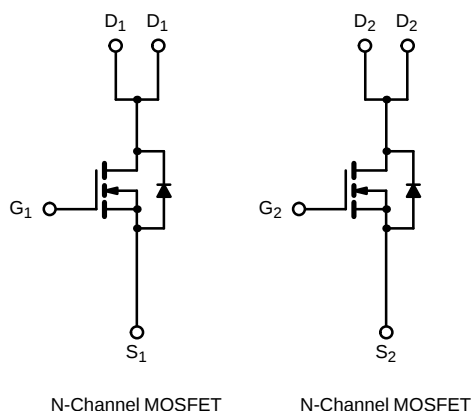
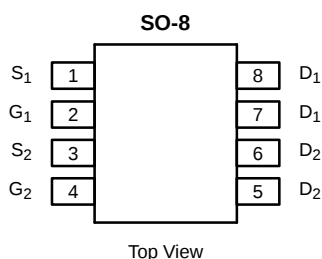




Dual N-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.03 @ $V_{GS} = 4.5$ V	± 6
	0.04 @ $V_{GS} = 2.5$ V	± 5.2



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 10	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	± 6	A
	$T_A = 70^\circ\text{C}$		± 4.8	
Pulsed Drain Current		I_{DM}	± 20	
Continuous Source Current (Diode Conduction) ^a		I_S	1.7	
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	2.0	W
	$T_A = 70^\circ\text{C}$		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

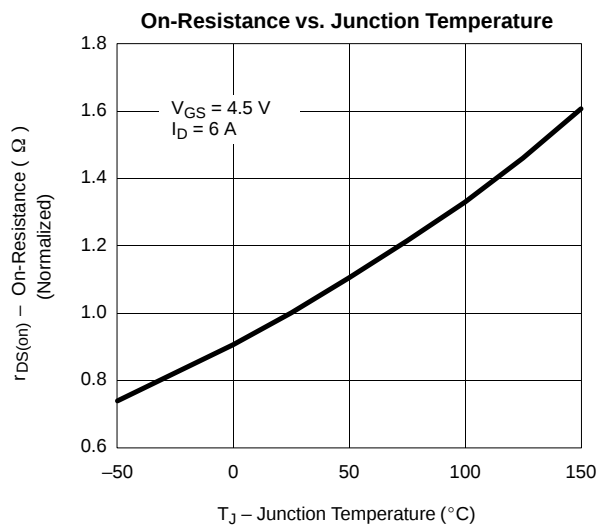
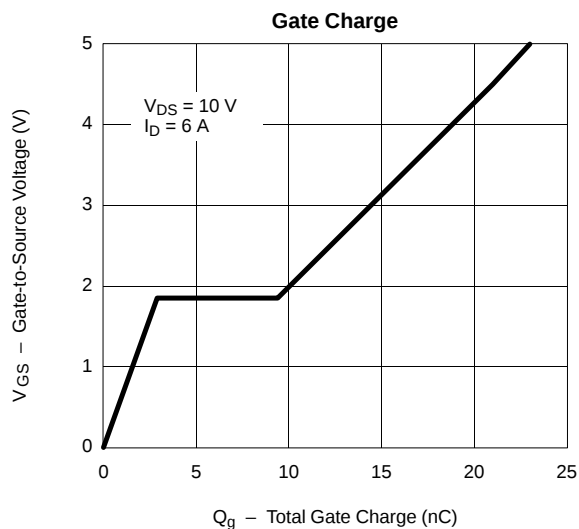
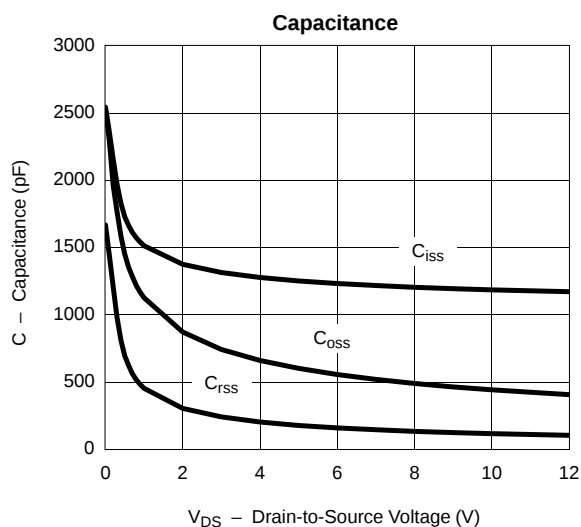
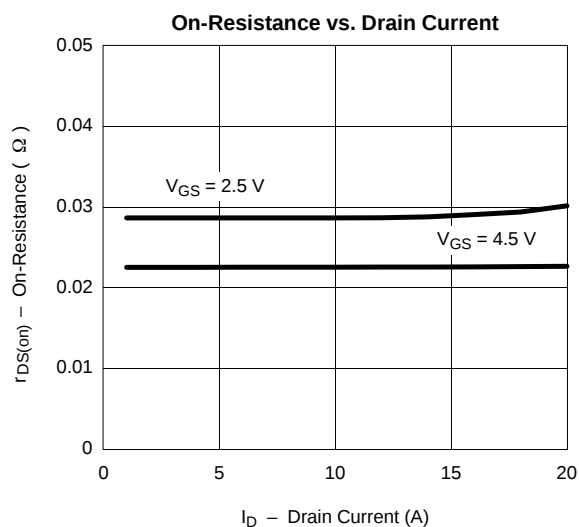
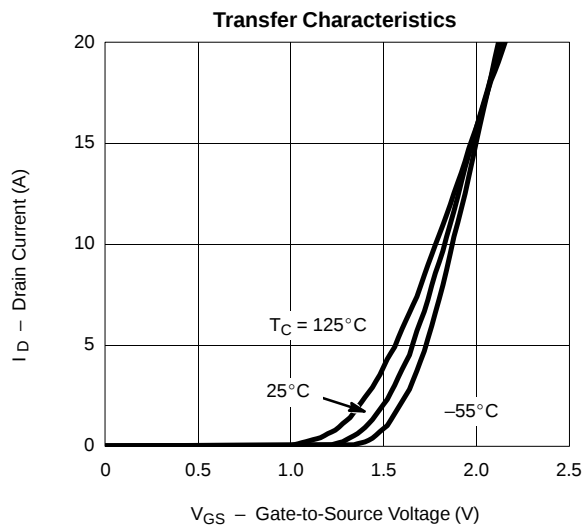
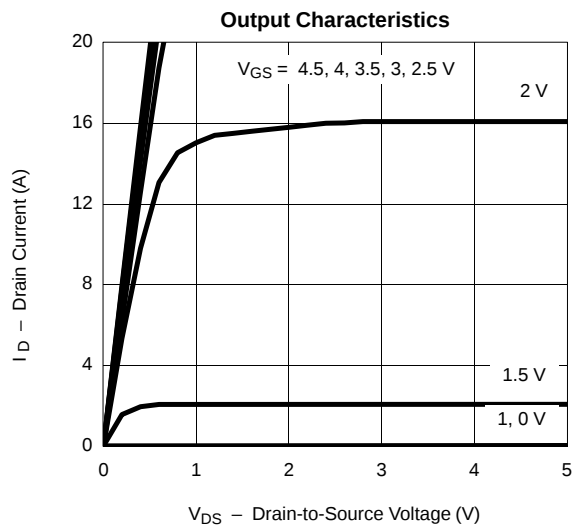
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static—0.6						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$			–1	μA
		$V_{DS} = 20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			–5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 4.5\ \text{V}$	20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\ \text{V}$, $I_D = 6\ \text{A}$		0.023	0.03	Ω
		$V_{GS} = 2.5\ \text{V}$, $I_D = 5.2\ \text{A}$		0.028	0.04	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\ \text{V}$, $I_D = 6\ \text{A}$		24		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\ \text{V}$, $V_{GS} = 4.5\ \text{V}$, $I_D = 6\ \text{A}$		21	40	nC
Gate-Source Charge	Q_{gs}			2.9		
Gate-Drain Charge	Q_{gd}			6.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\ \text{V}$, $R_L = 10\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 4.5\ \text{V}$, $R_G = 6\ \Omega$		30	60	ns
Rise Time	t_r			70	140	
Turn-Off Delay Time	$t_{d(off)}$			70	140	
Fall Time	t_f			30	60	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		70	100	

Notes

- Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

